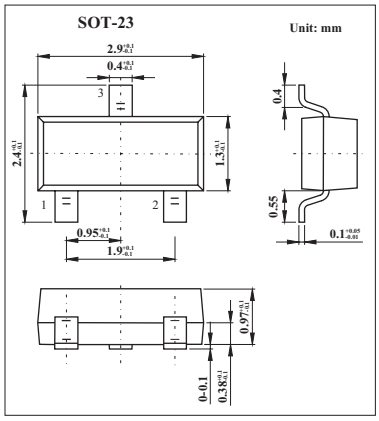
# SILICON SWITCHING DIODE

# 1SS221




## Features

- Low capacitance:$C_t$ = 4.0 pF MAX.
- High speed switching: $t_{rr}$ = 3.0 ns MAX.
- Wide applications including switching, limitter clipper.

## Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Peak Reverse Voltage | $V_{RM}$ | 100 | V |
| DC Reverse Voltage | $V_R$ | 100 | V |
| Peak Forward Current | $I_{FM}$ | 300 | mA |
| Average Rectified Current | $I_O$ | 100 | mA |
| DC Forward Current | P | 100 | mW |
| Junction Temperature | $T_j$ | 150 | ℃ |
| Storage Temperature Range | $T_{stg}$ | -55 + 150 | ℃ |
| Junction to Ambient | $R_{th(j-a)}$ | 0.67 | ℃/mW |

## Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Continuous reverse voltage | $V_F$ | $I_F$ = 10 Ma | | 720 | 850 | mV |
| | | $I_F$ = 50 mA | | 850 | 1000 | |
| | | $I_F$ = 100 mA | | 950 | 1200 | |
| Reverse current | $I_R$ | $V_R$ = 100 V | | | 1.0 | μA |
| capacitance | $C_t$ | $V_R$ = 0, f = 1.0 MHz | | 2.0 | 4.0 | pF |
| Reverse recovery time | $t_{rr}$ | $I_F$ = 10 mA,$V_R$ = 6 V, $R_L$ = 100Ω | | | 3.0 | ns |

## Marking

| Marking | A14 |
|---|---|